

Amended Claims

2. (currently amended) A method of increasing the holding voltage of a LVTSCR structure that includes an n-well and a p-well formed in a substrate, an n+ region and a p+ region formed in the n-well, and a n+ region formed in the p-well, the method comprising forming at least one p+ region and at least one additional n+ region inside a the p-well of the structure to define at least one p-n junction between the at least one p+ region and the at least one additional n+ region in the p-well that is forward biased during normal operation.
3. (currently amended) A method of increasing the holding voltage of a LVTSCR structure having an anode in an n-well and a cathode in a p-well, comprising providing an alternative current path from anode to cathode through at least one highly doped n+ region and at least one highly doped p+ region formed in the p-well of the structure, the at least one highly doped n+region and at least one highly doped p+ region formed in the p-well being forward biased relative to each other during normal operation other than purely the current path from anode to cathode through the p-material of the p-well.
4. (original) A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.
5. (canceled)
6. (currently amended) A method of claim 4, wherein at least one diode is formed in the p-well by the at least one highly doped n+ region and at least one highly doped p+ region, which provides a low resistance current path through the at least one diode once the threshold voltage across the at least one diode is exceeded.